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# 2SA1190, 2SA1191

Silicon PNP Epitaxial

# HITACHI

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## Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

## Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

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## 2SA1190, 2SA1191

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### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	2SA1190	2SA1191	Unit
Collector to base voltage	$V_{\text{CBO}}$	-90	-120	V
Collector to emitter voltage	$V_{\text{CEO}}$	-90	-120	V
Emitter to base voltage	$V_{\text{EBO}}$	-5	-5	V
Collector current	$I_{\text{C}}$	-100	-100	mA
Emitter current	$I_{\text{E}}$	100	100	mA
Collector power dissipation	$P_{\text{C}}$	400	400	mW
Junction temperature	$T_{\text{j}}$	150	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	-55 to +150	$^\circ\text{C}$

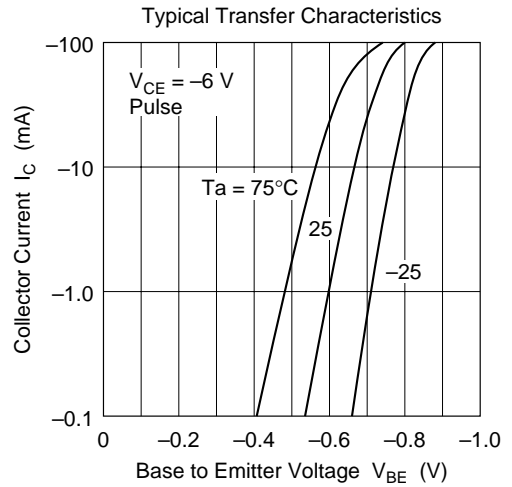
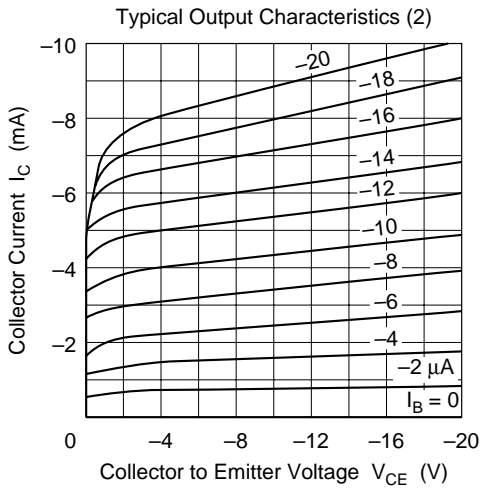
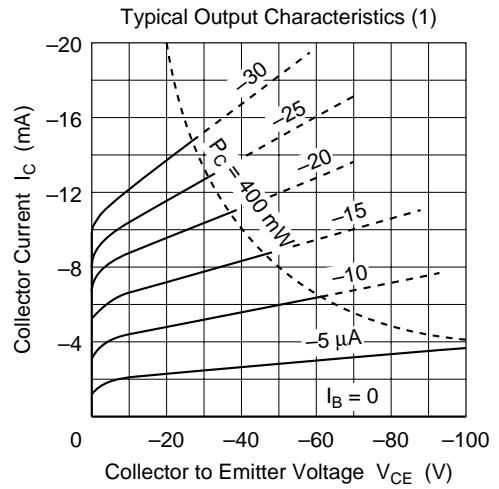
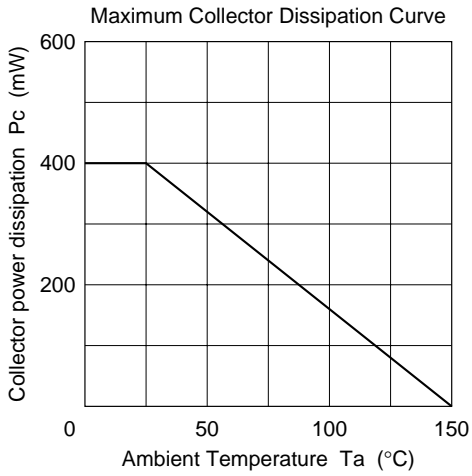
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA1190			2SA1191			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-0.1	—	—	-0.1	$\mu A$	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.1	—	—	-0.1	$\mu A$	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	250	—	800	250	—	800		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.05	-0.15	—	-0.05	-0.15	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	-0.7	-1.0	—	-0.7	-1.0	V	
Gain bandwidth product	$f_T$	—	130	—	—	130	—	MHz	$V_{CE} = -6 \text{ V}, I_C = -10 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	3.2	—	—	3.2	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Noise figure	NF	—	0.15	1.5	—	0.15	1.5	dB	$V_{CE} = -6 \text{ V}, I_C = -0.1 \text{ mA}, R_g = 10 \text{ k}\Omega, f = 1 \text{ kHz}$
		—	0.2	2.0	—	0.2	2.0	dB	$V_{CE} = -6 \text{ V}, I_C = -0.1 \text{ mA}, R_g = 10 \text{ k}\Omega, f = 10 \text{ Hz}$
Noise voltage referred to input	$e_n$	—	0.7	—	—	0.7	—	nV/ $\sqrt{\text{Hz}}$	$V_{CB} = -6 \text{ V}, I_C = -10 \text{ mA}, R_g = 0, f = 1 \text{ kHz}$

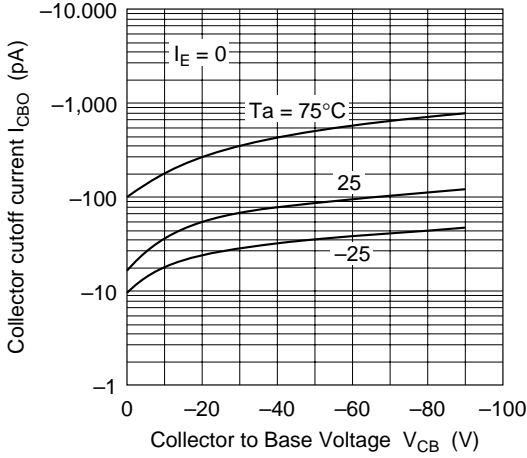
Notes: 1. The 2SA1190 and 2SA1191 are grouped by  $h_{FE}$  as follows.

2. Pulse test

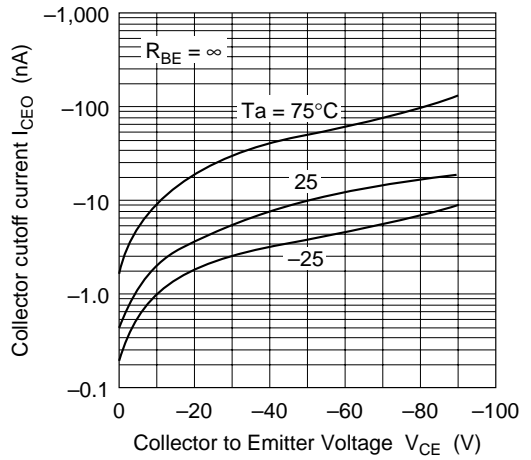
D	E
250 to 500	400 to 800



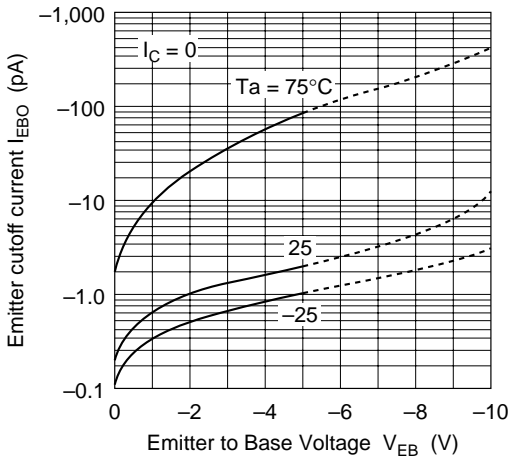
Collector Cutoff Current vs. Collector to Base Voltage



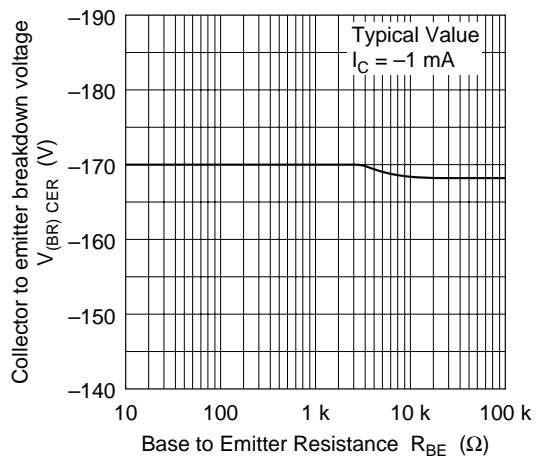
Collector Cutoff Current vs. Collector to Emitter Voltage



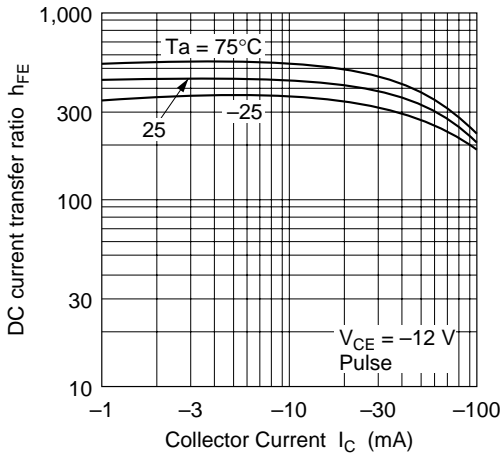
Emitter Cutoff Current vs. Emitter to Base Voltage



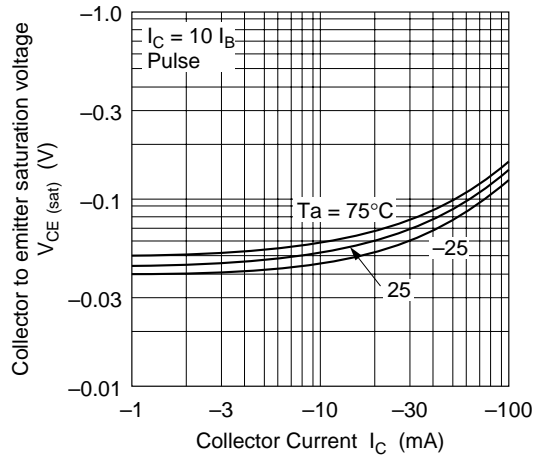
Collector to Emitter Breakdown Voltage vs. Base to Emitter Resistance



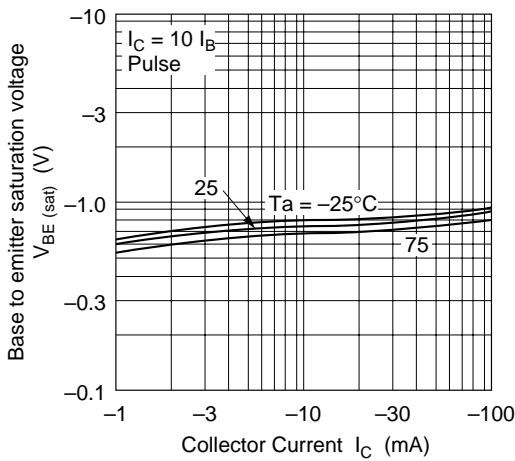
DC Current Transfer Ratio vs. Collector Current



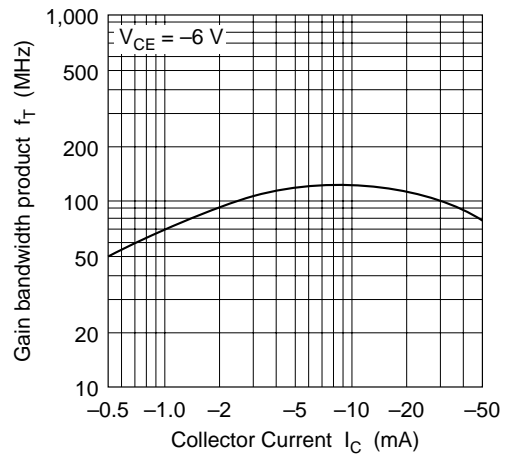
Collector to Emitter Saturation Voltage vs. Collector Current

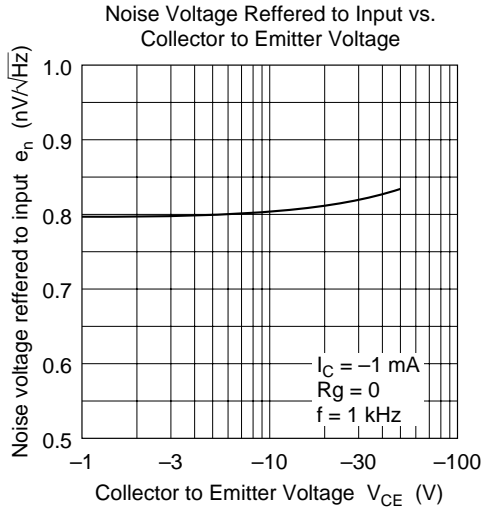
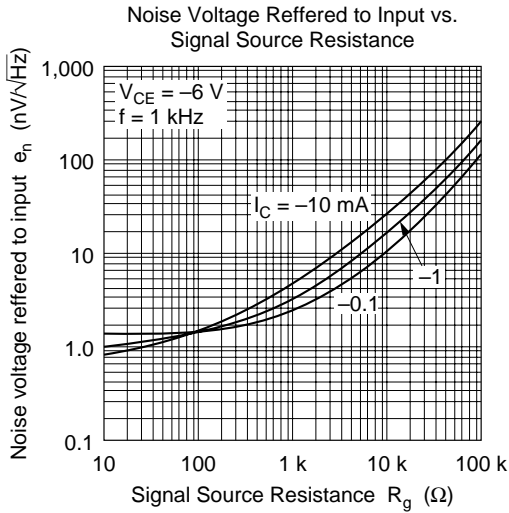
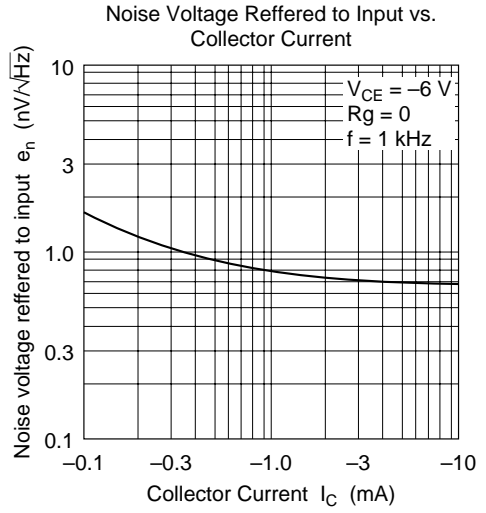
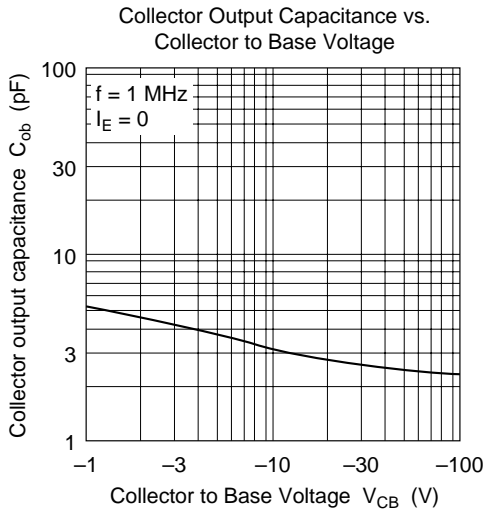


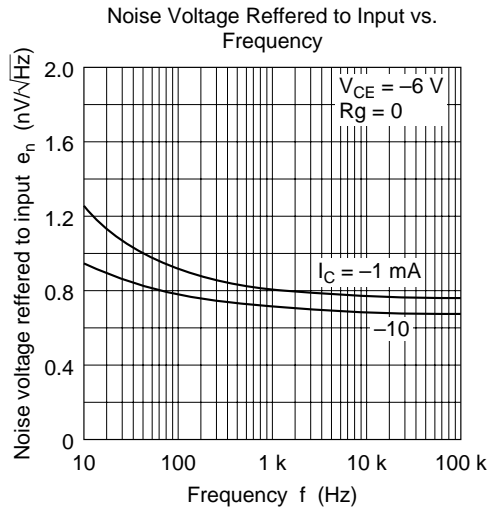
Base to Emitter Saturation Voltage vs. Collector Current



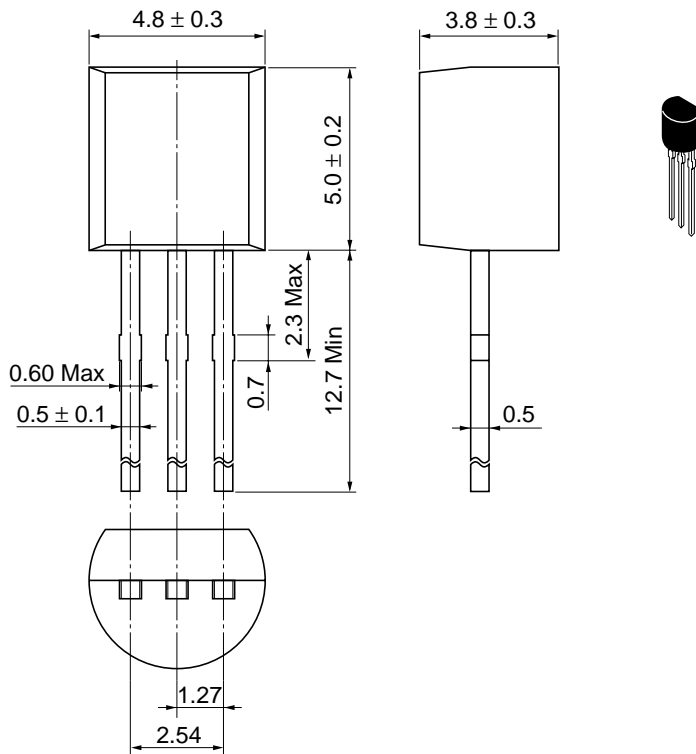
Gain Bandwidth Product vs. Collector Current











Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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